

IN THE SPECIFICATION:

Please insert the following new paragraph on page 1, before line 4.

This is a divisional application of Application No. 09/586,887, filed June 5, 2000.

Please insert the following paragraphs at page 7, between lines 16 and 17:

The above process may further comprise, between the steps (5) and (6), the step of forming a semiconductor junction on the surface of the semiconductor layer having been transferred to the second substrate.

The second substrate may comprise a flexible film, and force that acts in the direction where the film is separated from the first substrate may be applied to separate the semiconductor layer at the part of the porous layer. The flexible film may comprise a resinous film.

Please insert the following paragraphs at page 8, between lines 21 and 22:

The above process may further comprise, between the steps (6) and (7), the step of forming a semiconductor junction on the surface of the semiconductor layer having been transferred to the second substrate.

The second substrate may comprise a flexible film, and force that acts in the direction where the film is separated from the first substrate may be applied to separate the semiconductor layer at the part of the porous layer. The flexible film may comprise a resinous film.

Please amend the paragraph beginning at page 12, line 25 and ending at page 13, line 20, as follows:

Where the side of a wafer on which the semiconductor layer is formed is defined to be the surface and the other side the back, the semiconductor layer 104 formed on the porous layer 103 comes as follows: When, e.g., the surface portion is made porous in the state the periphery of the surface is shielded from the anodizing solution at the time of anodizing, and the epitaxial growth is carried out on the whole surface, what is formed in and on the wafer are, as shown in Fig. 3A, a porous layer 303, a flat single-crystal layer 305 formed when pores of the porous-layer surface portion are stopped up as a result of the hydrogen annealing carried out before the semiconductor layer is formed, and a single-crystal silicon semiconductor layer 304 formed by epitaxial growth. In order to separate the semiconductor layer to transfer it to a second substrate 308, the semiconductor layer 304, single-crystal layer 305 and porous layer 303 must be broken by separating force so as to reach a portion having the lowest breaking strength in the porous layer, and at this time the semiconductor layer 304 tends to be cracked or broken or to have other defects brought into it. The numeral 307 represents a cutting line.

Please amend the paragraph beginning at page 21, line 3 and ending at page 21, line 20, as follows:

As shown in Fig. 10A, first, into the surface portion (surface layer) of a single-crystal silicon substrate 1101, B (boron) is introduced by thermal diffusion or ion implantation or is incorporated when the substrate (wafer) is produced. The single-crystal

silicon substrate the surface layer (~~1202~~1102) of which has become p<sup>+</sup>-type is subjected to anodizing in, e.g., an aqueous HF solution to make the p<sup>+</sup>-type surface layer ~~1202~~1102 porous to form a porous layer 1103 (Fig. 10B). Here, the layer may be made porous such that the anodizing is carried out first at a level of low electric current and, after lapse of a certain time, at a level abruptly raised to high electric current and for a short time. This makes it possible to previously provide the porous layer with an internal structural change in density, whereby in a later step a silicon layer 1104 can be separated from the single-crystal silicon substrate 1101 with ease.

Please insert the following paragraph at page 22, between lines 20 and 21:

With regard to the anodizing apparatus shown in Fig. 14, 1501 is a semiconductor substrate; 1502 is an anodizing solution; 1503 is an anodizing solution bath; 1508 is a seal member; 1509 is a substrate holder; and 1510 is an electrode.

Please insert the following paragraph at page 29, between lines 25 and 26:

In more detail, 1601 is a semiconductor substrate; 1602 is an anodizing solution; 1603 is an anodizing solution bath; 1608 is a seal member; 1609 is a substrate holder; and 1610 and 1611 are electrodes.

Please amend the paragraph beginning at page 30, line 27 and ending at page 31, line 9, as follows:

After a grid electrode 1310 is formed on the surface of the porous layer 1309, a transparent polymeric-film substrate 1306 is bonded with an adhesive 1307 to the side of the single-crystal silicon substrate 1301 on which the silicon layers 1304 and 1305 have been formed, and these are put in an oven (not shown) and heated to bring the polymeric-film substrate 1306 and the silicon layer 1305 on the single-crystal silicon substrate 1301 into firm bond (Fig. 12F).

Please insert the following paragraph at page 36, between lines 3 and 4:

In more detail, 1401 is a semiconductor substrate; 1402 is an anodizing solution; 1403 is an anodizing solution bath; 1404 is an electrode for removing a peripheral portion (a cathode); 1405 is an electrode for removing a peripheral portion (an anode); 1406 is an electrode for forming an anti-reflection layer (a cathode); 1407 is an electrode for forming an anti-reflection layer (an anode); 1408 is a seal member; 1409 is a substrate holder; and 1410 and 1411 are electrodes.